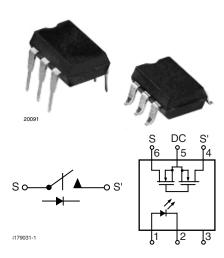
Vishay Semiconductors



1 Form A Solid State Relay



DESCRIPTION

The VO14642AT are high speed SPST normally open (1 form A) solid-state relay in a DIP-6 package. The relays are constructed as a multi-chip hybrid device. Actuation control is via an infrared LED. The output switch is a combination of a photodiode array with MOSFET switches. The relays can be configured for AC/DC or DC only operation.

FEATURES

- High speed SSR t_{on}/t_{off} < 800 μs
- Maximum R_{ON} 0.25 Ω
- Isolation test voltage 5300 V_{RMS}
- Load voltage 60 V
- Load current 2 A DC configuration
- DIP-6 package
- · Clean bounce free switching
- TTL/CMOS compatible input
- · Available on tape and reel
- · Pure tin leads
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- Instrumentation
- · Industrial controls
- Security

AGENCY APPROVALS

UL1577: file no. E52744 system code H or J,

double protection

file no. E52744 system code H or J, CUL - UL1577:

double protection

DIN EN: 60747-5-5

ORDER INFORMATION		
PART	REMARKS	PACKAGE
VO14642AABTR	Tape and reel	SMD-6
VO14642AT	Tubes	DIP-6

ABSOLUTE MAXIMUM RATINGS (1)									
PARAMETER	TEST CONDITION SYMBOL VALUE U								
INPUT	INPUT								
LED continous forward current		I _F	50	mA					
LED reverse voltage		V_{R}	5.0	V					
LED power dissipation	at 25 °C	P _{diss}	80	mW					
OUTPUT									
DC or peak AC load voltage		V_{L}	60	V					
Output power dissipation	at 25 °C	P _{diss}	250	mW					







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ABSOLUTE MAXIMUM RATINGS (1)									
PARAMETER TEST CONDITION SYMBOL VALUE UNIT									
COUPLER									
Total power dissipation		P _{diss}	330	mW					
Ambient temperature range		T _{amb}	- 40 to + 85	°C					
Storage temperature range		T _{stg}	- 40 to + 125	°C					
Soldering temperature (2)	t ≤ 10 s max.	T _{sld}	260	°C					
Isolation test voltage	for 1.0 s	V _{ISO}	3750	V _{RMS}					

Notes

ABSOLUTE MAXIMUM RATING CURVE

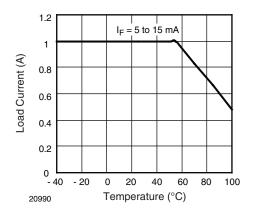


Fig. 1 - I_{LOAD} vs. Temperature

THERMAL CHARACTERISTICS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Maximum LED junction temperature	at 25 °C	T _{jmax}	125	°C
Maximum output die junction temperature	at 25 °C	T _{jmax}	125	°C
Thermal resistance, junction emitter to board	at 25 °C	$\theta_{\sf EB}$	176	°C/W
Thermal resistance, junction emitter to case	at 25 °C	$\theta_{\sf EC}$	208	°C/W
Thermal resistance, junction detector to board	at 25 °C	θ_{DB}	67	°C/W
Thermal resistance, junction detector to case	at 25 °C	θ_{DC}	134	°C/W
Thermal resistance, junction emitter to junction detector	at 25 °C	$\theta_{\sf ED}$	310	°C/W
Thermal resistance, case to ambient	at 25 °C	$\theta_{\sf CA}$	2180	°C/W

Note

The thermal model is represented in the thermal network below. Each resistance value given in this model can be used to calculate the temperatures at each node for a given operating condition. The thermal resistance from board to ambient will be dependent on the type of PCB, layout and thickness of copper traces. For a detailed explanation of the thermal model, please reference Vishay's thermal characteristics of optocouplers application note.

 $^{^{(1)}}$ T_{amb} = 25 °C, unless otherwise specified.

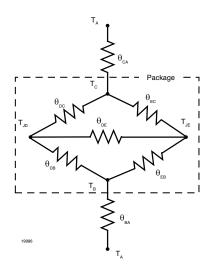
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

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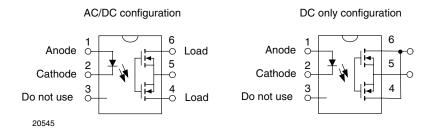
ELECTRICAL CHARACTERISTICS							
PARAMETER	TEST CONDITION SYMBOL		MIN.	TYP.	MAX.	UNIT	
INPUT							
LED forward current, switch turn-on	$I_L=1~A,~V_L\leq 0.5~V,~t=10~ms$	I _{Fon}		0.5	2.0	mA	
LED forward current, switch to remain off	$V_L = 60 \text{ V}, I_L < 1 \mu\text{A}$	I _{Foff}	50			μΑ	
Input reverse current	V _R = 5 V	I _R			10	μΑ	
LED forward voltage	I _F = 10 mA	V_{F}	1.0	1.3	1.5	V	
OUTPUT							
Peak load voltage		V_{L}			60	V	
Load current DC	I _F = 10 mA	ΙL			2	Α	
Peak load current (AC/DC)	10 ms	I _{LPK}			3.6	Α	
On-resistance (AC/DC)	I _F = 10 mA, I _L = 1 A	R _{ON}		0.18	0.25	Ω	
On-resistance (DC only)	I _F = 10 mA, I _L = 2 A	R _{ON}		0.05	0.07	Ω	
Off-state leakage current	$I_F = 0 \text{ mA}, V_L = 60 \text{ V}$	I _{LEAK}			1	μΑ	

Note

T_{amb} = 25 °C, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

PIN CONFIGURATION

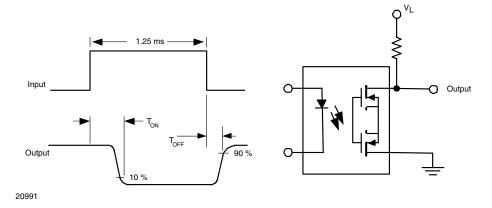




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SWITCHING CHARACTERISTICS (AC/DC CONNECTION)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Turn-on time	$I_F = 10 \text{ mA}, V_L = 30 \text{ V}, I_L = 200 \text{ mA}$	t _{on1}		370	800	μs	
Turn-off time	$I_F = 10 \text{ mA}, V_L = 30 \text{ V}, I_L = 200 \text{ mA}$	t _{off1}		50	800	μs	
Turn-on time	$I_F = 10 \text{ mA}, V_L = 5 \text{ V}, I_L = 1 \text{ A}$	t _{on2}		550		μs	
Turn-off time	$I_F = 10 \text{ mA}, V_L = 5 \text{ V}, I_L = 1 \text{ A}$	t _{off2}		18		μs	



PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Climatic classification		IEC 68 part 1			40/85/21		
Pollution degree		DIN VDE 0109			2		
Tracking resistance (comparative t	racking index)	Insulation group IIIa	CTI	175			
Highest allowable overvoltage		Transient overvoltage	V_{IOTM}	8000			V _{peak}
Maximum working insulation voltage	je	Recurring peak voltage	V_{IORM}	890			V_{peak}
Insulation resistance at 25 °C		V _{IO} = 500 V	R _{IS}			≥ 10 ¹²	Ω
Insulation resistance at T _S		V _{IO} = 500 V	R _{IS}			≥ 10 ⁹	Ω
Insulation resistance at 100 °C		V _{IO} = 500 V	R _{IS}			≥ 10 ¹¹	Ω
Partial discharge test voltage		Method b, $V_{pd} = V_{IORM} \times 1.875$	V_{pd}			1669	V _{peak}
Isolation test voltage		1 s	V _{ISO}			5300	V _{RMS}
Safety limiting values -	Case temperature		T _{SI}		165		°C
maximum values allowed in the	Input current		I _{SI}		150		mA
event of a failure	Output power		P _{SO}		400		mW
Minimum external air gap (clearance distance)		Measured from input terminals to output terminals, shortest distance through air			≥ 7.0		mm
Minimum external tracking (creepage distance)		Measured from input terminals to output terminals, shortest distance path along body			≥ 7.0		mm

Note

This SSR is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

Vishay Semiconductors

1 Form A Solid State Relay



TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

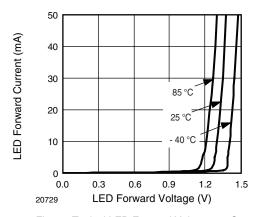


Fig. 2 - Typical LED Forward Voltage vs. Current

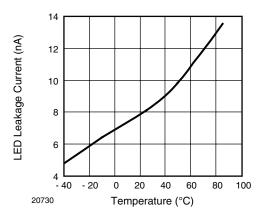


Fig. 3 - Typical LED Leakage vs. Temperature ($V_R = 5 V$)

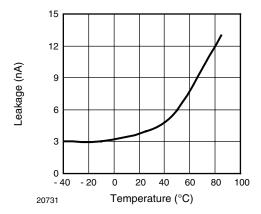


Fig. 4 - Typical Leakage vs. Temperature ($V_{Load} = 60 \text{ V}$)

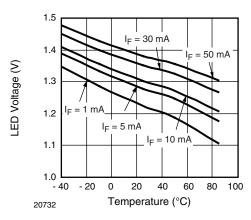


Fig. 5 - Typical LED Forward Voltage vs. Temperature

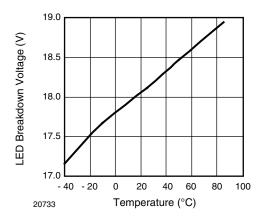


Fig. 6 - Typical Breakdown Voltage vs. Temperatur ($I_L = 5 \mu A$)

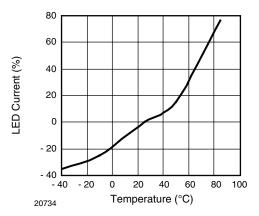


Fig. 7 - I_F For Switch Operation vs. Temperature (Normalized to 25 °C, Load Current = 1 A)



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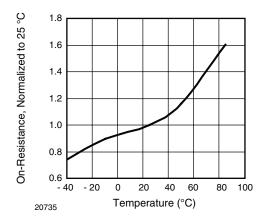


Fig. 8 - Typical On-Resistance vs. Temperature (Load Current = 1 A)

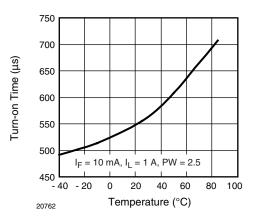


Fig. 11 - Typical Turn-On vs. Temperature (Load Current = 1 A)

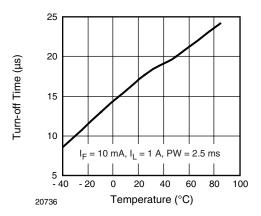


Fig. 9 - Typical Turn-Off vs. Temperature (Load Current = 1 A)

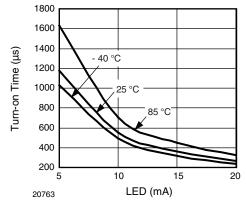


Fig. 12 - Typical Turn-On vs. LED Forward Current (Load Current = 1 A)

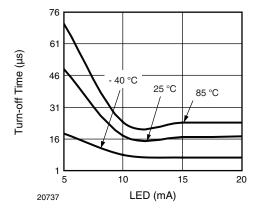


Fig. 10 - Typical Turn-Off vs. LED Forward Current (Load Current = 1 A)

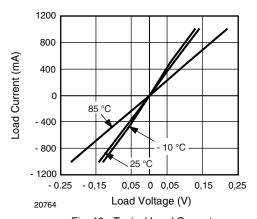


Fig. 13 - Typical Load Current vs. Load Voltage (LED Current = 10 mA)



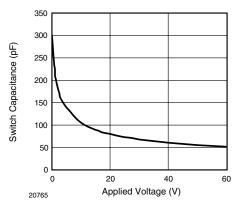
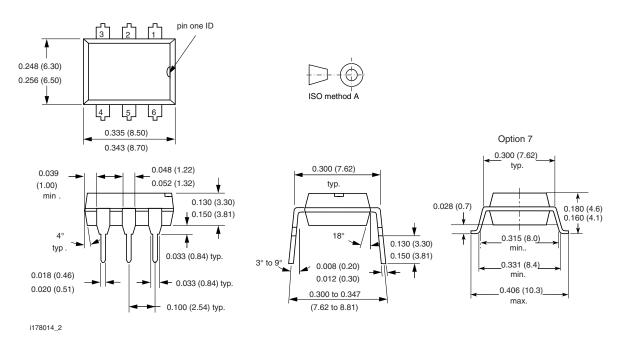


Fig. 14 - Switch Capacitance vs. Applied Voltage

PACKAGE DIMENSIONS in inches (millimeters)





VO14642AT/VO14642AABTR

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OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

Document Number: 81646 Rev. 1.2, 07-May-08



Vishay

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